

0.5 A Output Current IGBT and MOSFET Driver



19813



FEATURES

- 0.5 A minimum peak output current
- 25 kV/ μ s minimum common mode rejection (CMR) at $V_{CM} = 1500$ V
- $I_{CC} = 2.5$ mA maximum supply current
- Under voltage lock-out (UVLO) with hysteresis
- Wide operating V_{CC} range: 15 V to 32 V
- 0.4 μ s maximum propagation delay
- Industrial temperature range: - 40 °C to 110 °C
- 0.5 V maximum low level output voltage (V_{OL})
- Compliant to RoHS directive 2002/95/EC


RoHS
COMPLIANT

DESCRIPTION

The VO3150A consists of a LED optically coupled to an integrated circuit with a power output stage. This optocoupler is ideally suited for driving power IGBTs and MOSFETs used in motor control inverter applications. The high operating voltage range of the output stage provides the drive voltages required by gate controlled devices. The voltage and current supplied by this optocoupler makes it ideally suited for directly driving IGBTs with ratings up to 800 V/20 A. For IGBTs with higher ratings, the VO3150A can be used to drive a discrete power stage which drives the IGBT gate.

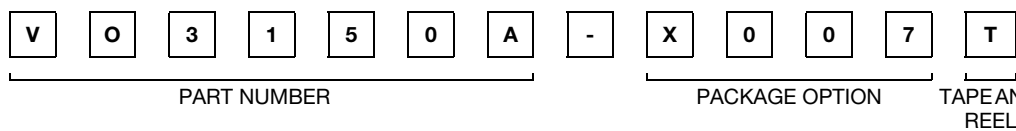
APPLICATIONS

- Isolated IGBT/MOSFET gate driver
- AC and brushless DC motor drives
- Induction stove top
- Industrial inverters
- Switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

AGENCY APPROVALS

- UL - file no. E52744 system code H, double protection
- cUL - file no. E52744, equivalent to CSA bulletin 5A
- DIN EN 60747-5-5 (VDE0884) available with option 1

ORDERING INFORMATION



| PACKAGE | UL, cUL | UL, cUL, VDE |
|-----------------|---------------|---------------|
| DIP-8 | VO3150A | - |
| SMD-8, option 7 | VO3150A-X007T | VO3150A-X017T |

TRUTH TABLE

| LED | $V_{CC} - V_{EE}$ "POSITIVE GOING" (TURN ON) | $V_{CC} - V_{EE}$ "NEGATIVE GOING" (TURN OFF) | V_O |
|-----|--|---|------------|
| Off | 0 V to 32 V | 0 V to 32 V | Low |
| On | 0 V to 11 V | 0 V to 9.5 V | Low |
| On | 11 V to 13.5 V | 9.5 V to 12 V | Transition |
| On | 13.5 V to 32 V | 12 V to 32 V | High |

| ABSOLUTE MAXIMUM RATINGS ⁽¹⁾ ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified) | | | | |
|---|--|---------------------|-----------------|--------------------|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
| INPUT | | | | |
| Input forward current | | I_F | 25 | mA |
| Peak transient input current | < 1 μs pulse width, 300 pps | $I_{F(TRAN)}$ | 1 | A |
| Reverse input voltage | | V_R | 5 | V |
| Output power dissipation | | P_{diss} | 45 | mW |
| OUTPUT | | | | |
| High peak output current ⁽²⁾ | | $I_{OH(PEAK)}$ | 0.5 | A |
| Low peak output current ⁽²⁾ | | $I_{OL(PEAK)}$ | 0.5 | A |
| Supply voltage | | $(V_{CC} - V_{EE})$ | 0 to + 35 | V |
| Output voltage | | $V_{O(PEAK)}$ | 0 to + V_{CC} | V |
| Output power dissipation | | P_{diss} | 250 | mW |
| OPTOCOUPLER | | | | |
| Isolation test voltage (between emitter and detector, climate per DIN 500414, part 2, Nov. 74) | $t = 1\text{ s}$ | V_{ISO} | 5300 | V_{RMS} |
| Storage temperature range | | T_S | - 55 to + 125 | $^{\circ}\text{C}$ |
| Ambient operating temperature range | | T_{amb} | - 40 to + 110 | $^{\circ}\text{C}$ |
| Total power dissipation | | P_{tot} | 295 | mW |
| Lead solder temperature ⁽³⁾ | for 10 s, 1.6 mm below seating plane | T_{sld} | 260 | $^{\circ}\text{C}$ |

Notes

- ⁽¹⁾ Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.
- ⁽²⁾ Maximum pulse width = 10 μs , maximum duty cycle = 0.2 %. This value is intended to allow for component tolerances for designs with I_O peak minimum = 0.5 A. See applications section for additional details on limiting I_{OH} peak.
- ⁽³⁾ Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

| RECOMMENDED OPERATING CONDITION | | | | |
|--|-------------------|------|-------|--------------------|
| PARAMETER | SYMBOL | MIN. | MAX. | UNIT |
| Power supply voltage | $V_{CC} - V_{EE}$ | 15 | 32 | V |
| Input LED current (on) | I_F | 7 | 16 | mA |
| Input voltage (off) | $V_{F(OFF)}$ | - 3 | 0.8 | V |
| Operating temperature | T_{amb} | - 40 | + 110 | $^{\circ}\text{C}$ |

| THERMAL CHARACTERISTICS | | | |
|---|----------------|-------|------|
| PARAMETER | SYMBOL | VALUE | UNIT |
| LED power dissipation | P_{diss} | 45 | mW |
| Output power dissipation | P_{diss} | 250 | mW |
| Total power dissipation | P_{tot} | 285 | mW |
| Maximum LED junction temperature | T_{Jmax} | 125 | °C |
| Maximum output die junction temperature | T_{Jmax} | 125 | °C |
| Thermal resistance, junction emitter to board | θ_{JEB} | 169 | °C/W |
| Thermal resistance, junction emitter to case | θ_{JEC} | 192 | °C/W |
| Thermal resistance, junction detector to board | θ_{JDB} | 82 | °C/W |
| Thermal resistance, junction detector to case | θ_{JDC} | 80 | °C/W |
| Thermal resistance, junction emitter to junction detector | θ_{JED} | 200 | °C/W |
| Thermal resistance, case to ambient | θ_{CA} | 2645 | °C/W |


Note

- The thermal model is represented in the thermal network below. Each resistance value given in this model can be used to calculate the temperatures at each node for a given operating condition. The thermal resistance from board to ambient will be dependent on the type of PCB, layout and thickness of copper traces. For a detailed explanation of the thermal model, please reference Vishay's Thermal Characteristics of Optocouplers application note.

| ELECTRICAL CHARACTERISTICS (1) | | | | | | |
|--|--|---------------------------|--------------|----------------|------|-------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| High level output current | $I_F = 16 \text{ mA}$, $R_g = 10 \Omega$, $C_g = 20 \text{ nF}$, $V_{CC} = 15 \text{ V}$, $V_{EE} = 0 \text{ V}$ | I_{OH} (3) | 0.5 | | | A |
| Low level output current | $I_F = 0 \text{ mA}$, $R_g = 10 \Omega$, $C_g = 20 \text{ nF}$, $V_{CC} = 15 \text{ V}$, $V_{EE} = 0 \text{ V}$ | I_{OL} (3) | 0.5 | | | A |
| High level output voltage | $I_O = -100 \text{ mA}$ | V_{OH} (4) | $V_{CC} - 4$ | $V_{CC} - 2.1$ | | V |
| Low level output voltage | $I_O = 100 \text{ mA}$ | V_{OL} | | 0.2 | 0.5 | V |
| High level supply current | Output open, $I_F = 7 \text{ mA}$ to 16 mA | I_{CCH} | | | 2.5 | mA |
| Low level supply current | Output open, $V_F = -3 \text{ V}$ to $+0.8 \text{ V}$ | I_{CCL} | | | 2.5 | mA |
| Threshold input current low to high | $I_O = 0 \text{ mA}$, $V_O > 5 \text{ V}$ | I_{FLH} | | 2.1 | 5 | mA |
| Threshold input voltage high to low | | V_{FHL} | 0.8 | | | V |
| Input forward voltage | $I_F = 10 \text{ mA}$ | V_F | 1 | 1.3 | 1.6 | V |
| Temperature coefficient of forward voltage | $I_F = 10 \text{ mA}$ | $\Delta V_F / \Delta T_A$ | | -1.4 | | mV/°C |
| Input reverse breakdown voltage | $I_R = 10 \mu\text{A}$ | BVP | 5 | | | V |
| Input capacitance | $f = 1 \text{ MHz}$, $V_F = 0 \text{ V}$ | C_{IN} | | 60 | | pF |
| UVLO threshold | $V_O \geq 5 \text{ V}$ | V_{UVLO+} | 11 | 12.6 | 13.5 | V |
| | $I_F = 10 \text{ mA}$ | V_{UVLO-} | 9.5 | 10.7 | 12 | V |
| UVLO hysteresis | | $UVLO_{HYS}$ | | 1.9 | | V |

Notes

- Minimum and maximum values were tested over recommended operating conditions ($T_{amb} = -40 \text{ °C}$ to 110 °C , $I_{F(ON)} = 7 \text{ mA}$ to 16 mA , $V_{F(OFF)} = -3 \text{ V}$ to 0.8 V , $V_{CC} = 15 \text{ V}$ to 32 V , $V_{EE} = \text{ground}$) unless otherwise specified. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements. All typical values were measured at $T_{amb} = 25 \text{ °C}$ and with $V_{CC} - V_{EE} = 32 \text{ V}$.
- Maximum pulse width = $50 \mu\text{s}$, maximum duty cycle = 0.5% .
- Maximum pulse width = $10 \mu\text{s}$, maximum duty cycle = 0.2% . This value is intended to allow for component tolerances for designs with I_O peak minimum = 0.5 A .
- In this test V_{OH} is measured with a dc load current. When driving capacitive loads V_{OH} will approach V_{CC} as I_{OH} approaches zero A. Maximum pulse width = 1 ms , maximum duty cycle = 20% .

TEST CIRCUITS

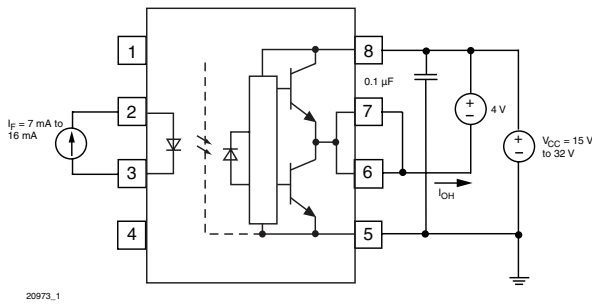


Fig. 1 - I_{OH} Test Circuit



Fig. 4 - V_{OL} Test Circuit

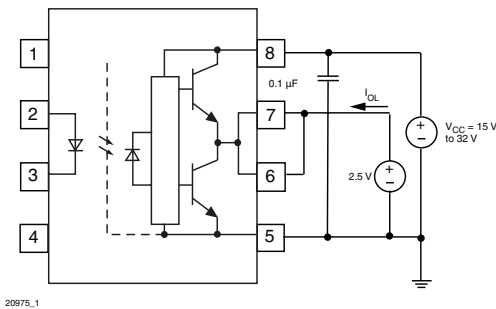


Fig. 2 - I_{OL} Test Circuit



Fig. 5 - I_{FLH} Test Circuit

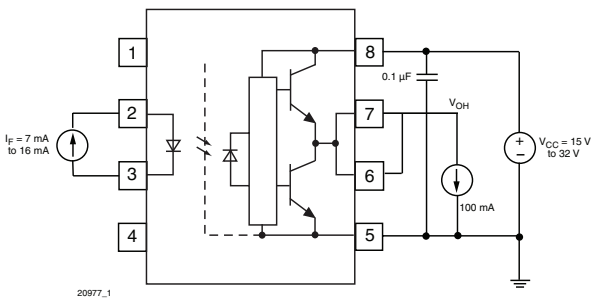


Fig. 3 - V_{OH} Test Circuit



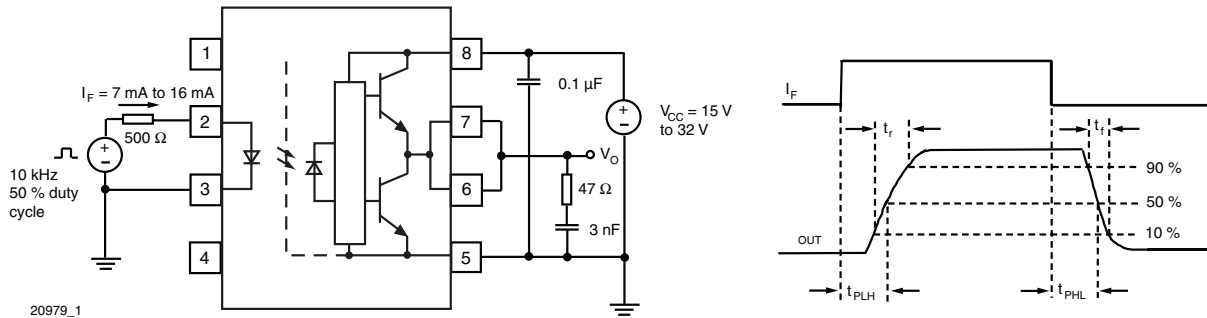
Fig. 6 - UVLO Test Circuit

| SWITCHING CHARACTERISTICS | | | | | | |
|---|---|-----------------------------|--------|------|------|---------------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Propagation delay time to logic low output ⁽¹⁾ | $R_g = 47 \Omega$, $C_g = 3 \text{ nF}$, $f = 10 \text{ kHz}$, duty cycle = 50 % | t_{PHL} | 0.1 | | 0.4 | μs |
| Propagation delay time to logic high output ⁽¹⁾ | $R_g = 47 \Omega$, $C_g = 3 \text{ nF}$, $f = 10 \text{ kHz}$, duty cycle = 50 % | t_{PLH} | 0.1 | | 0.4 | μs |
| Pulse width distortion ⁽²⁾ | $R_g = 47 \Omega$, $C_g = 3 \text{ nF}$, $f = 10 \text{ kHz}$, duty cycle = 50 % | PWD | | | 0.2 | μs |
| Propagation delay difference between any two parts ⁽³⁾ | $R_g = 47 \Omega$, $C_g = 3 \text{ nF}$, $f = 10 \text{ kHz}$, duty cycle = 50 % | PDD ($t_{PHL} - t_{PLH}$) | - 0.35 | | 0.35 | μs |
| Rise time | $R_g = 47 \Omega$, $C_g = 3 \text{ nF}$, $f = 10 \text{ kHz}$, duty cycle = 50 % | t_r | | 0.1 | | μs |
| Fall time | $R_g = 47 \Omega$, $C_g = 3 \text{ nF}$, $f = 10 \text{ kHz}$, duty cycle = 50 % | t_f | | 0.1 | | μs |

| SWITCHING CHARACTERISTICS | | | | | | |
|---------------------------|---|----------------|------|------|------|---------------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| UVLO turn on delay | $V_O > 5\text{ V}$, $I_F = 10\text{ mA}$ | $T_{UVLO-ON}$ | | 0.8 | | μs |
| UVLO turn off delay | $V_O > 5\text{ V}$, $I_F = 10\text{ mA}$ | $T_{UVLO-OFF}$ | | 0.6 | | μs |

Notes

- (1) This load condition approximates the gate load of a 1200 V/25 A IGBT.
- (2) Pulse width distortion (PWD) is defined as $|t_{pHL} - t_{pLH}|$ for any given device.
- (3) The difference between t_{pHL} and t_{pLH} between any two VO3150A parts under the same test condition.


 Fig. 7 - t_{pLH} , t_{pHL} , t_r and t_f Test Circuit and Waveforms

| COMMON MODE TRANSIENT IMMUNITY | | | | | | |
|---|--|----------|------|------|------|-------------------------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Common mode transient immunity at logic high output ⁽¹⁾⁽²⁾ | $T_A = 25\text{ }^\circ\text{C}$, $I_F = 10\text{ mA to }16\text{ mA}$, $V_{CM} = 1500\text{ V}$, $V_{CC} = 32\text{ V}$ | $ CM_H $ | 25 | 35 | | $\text{kV}/\mu\text{s}$ |
| Common mode transient immunity at logic low output ⁽¹⁾⁽³⁾ | $T_A = 25\text{ }^\circ\text{C}$, $V_{CM} = 1500\text{ V}$, $V_{CC} = 32\text{ V}$, $V_F = 0\text{ V}$ | $ CM_L $ | 25 | 35 | | $\text{kV}/\mu\text{s}$ |

Notes

- (1) Pins 1 and 4 need to be connected to LED common.
- (2) Common mode transient immunity in the high state is the maximum tolerable $|dV_{CM}/dt|$ of the common mode pulse, V_{CM} , to assure that the output will remain in the high state (i.e., $V_O > 15\text{ V}$).
- (3) Common mode transient immunity in a low state is the maximum tolerable $|dV_{CM}/dt|$ of the common mode pulse, V_{CM} , to assure that the output will remain in a low state (i.e., $V_O < 1\text{ V}$).

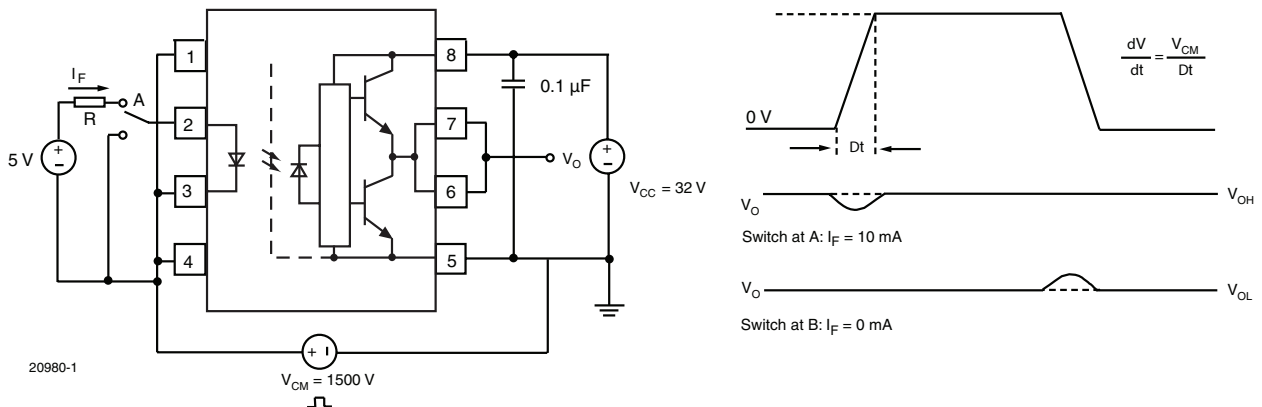


Fig. 8 - CMR Test Circuit and Waveforms

| SAFETY AND INSULATION RATINGS | | | | | | |
|--|----------------|--------|------|-----------|------|------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Climatic classification (according to IEC 68 part 1) | | | | 40/110/21 | | |
| Comparative tracking index | | CTI | 175 | | 399 | |
| V_{IOTM} | | | 8000 | | | V |
| V_{IORM} | | | 890 | | | V |
| P_{SO} | | | | | 500 | mW |
| I_{SI} | | | | | 300 | mA |
| T_{SI} | | | | | 175 | °C |
| Creepage distance | Standard DIP-8 | | 7 | | | mm |
| Clearance distance | Standard DIP-8 | | 7 | | | mm |
| Creepage distance | 400 mil DIP-8 | | 8 | | | mm |
| Clearance distance | 400 mil DIP-8 | | 8 | | | mm |

Note

- As per IEC 60747-5-5, §7.4.3.8.1, this optocoupler is suitable for “safe electrical insulation” only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

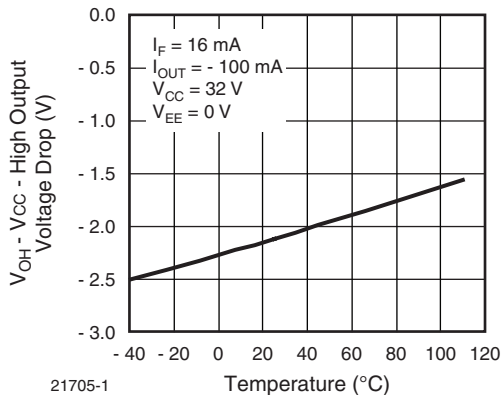


Fig. 9 - High Output Voltage Drop vs. Temperature

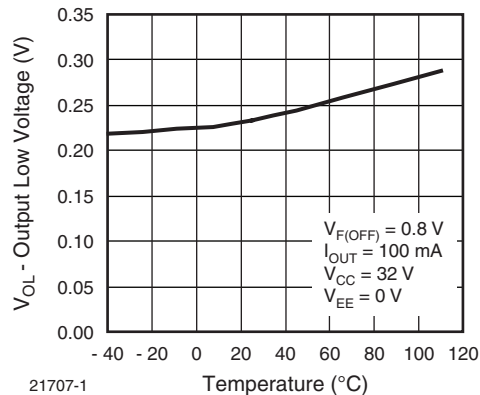


Fig. 11 - Output Low Voltage vs. Temperature

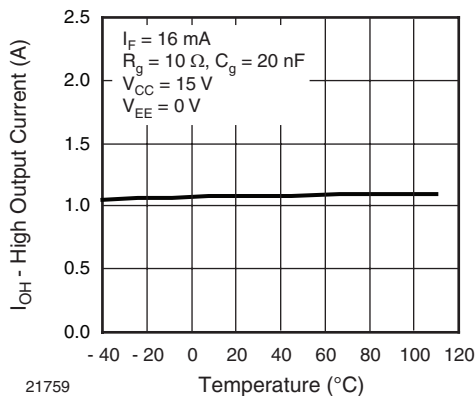


Fig. 10 - High Output Current vs. Temperature

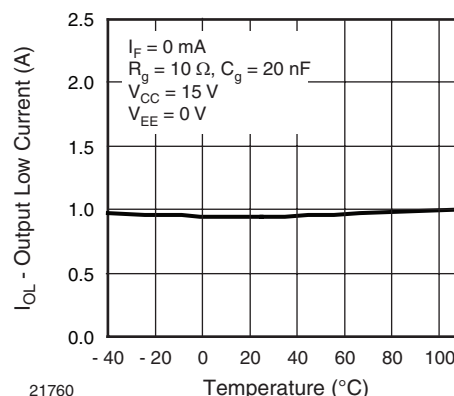


Fig. 12 - Output Low Current vs. Temperature



Fig. 13 - Output Low Voltage vs. Output Low Current

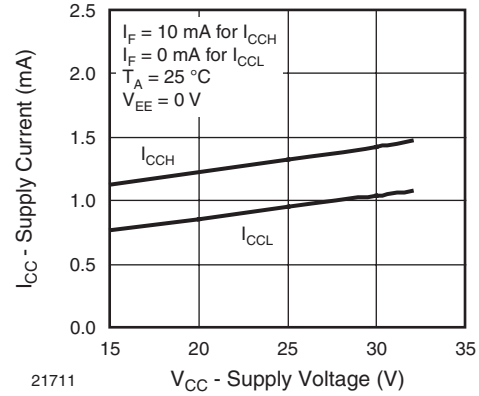


Fig. 16 - Supply Current vs. Supply Voltage

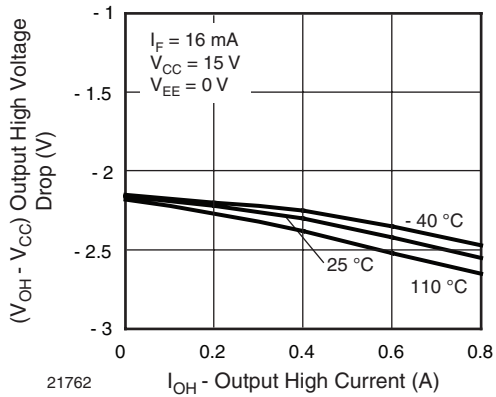


Fig. 14 - Output High Voltage Drop vs. Output High Current

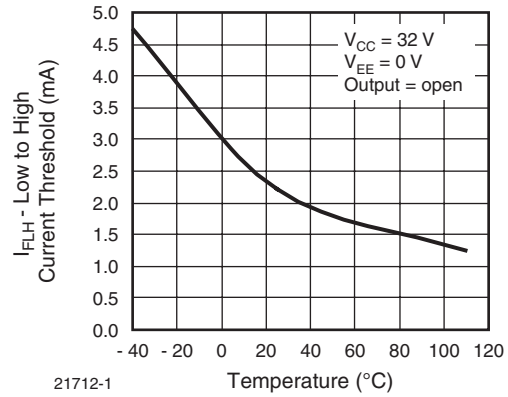


Fig. 17 - Low to High Current Threshold vs. Temperature

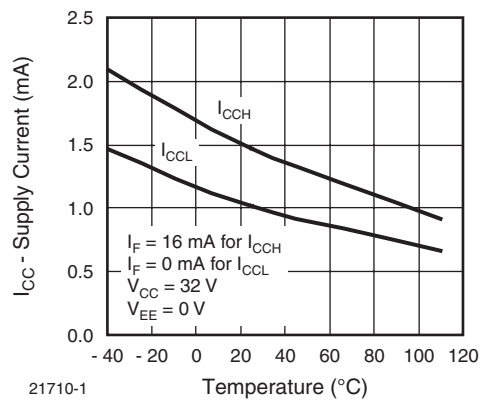


Fig. 15 - Supply Current vs. Temperature

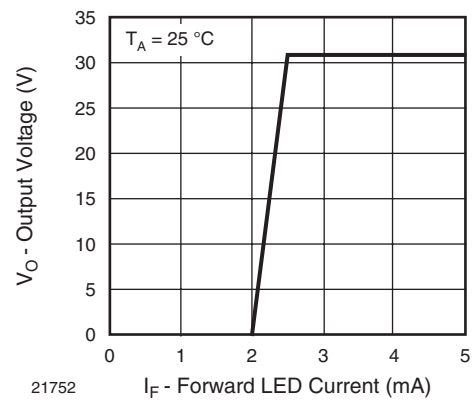


Fig. 18 - Transfer Characteristics

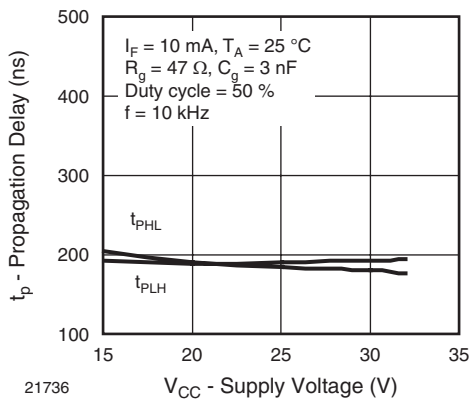


Fig. 19 - Propagation Delay vs. Supply Voltage

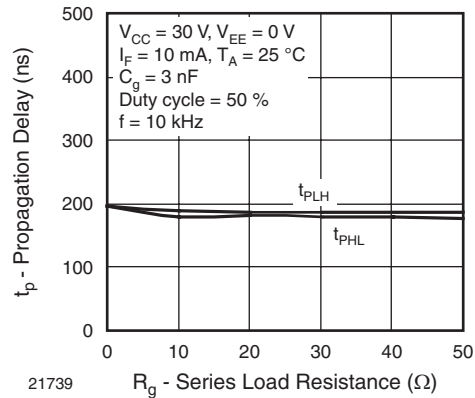


Fig. 22 - Propagation Delay vs. Series Load Resistance

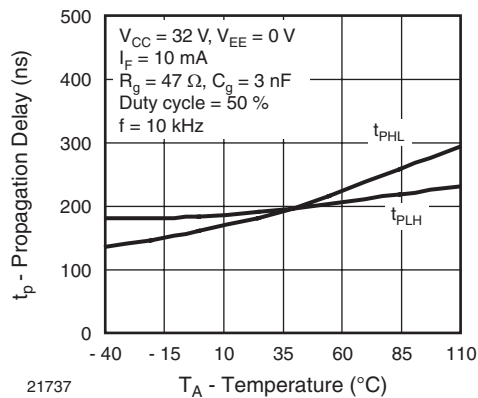


Fig. 20 - Propagation Delay vs. Temperature

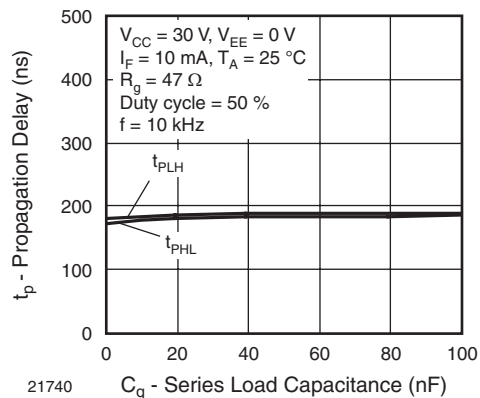


Fig. 23 - Propagation Delay vs. Series Load Capacitance

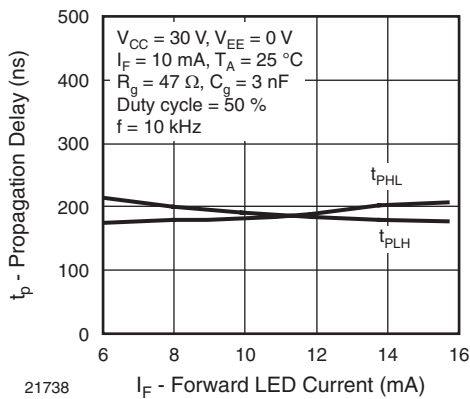
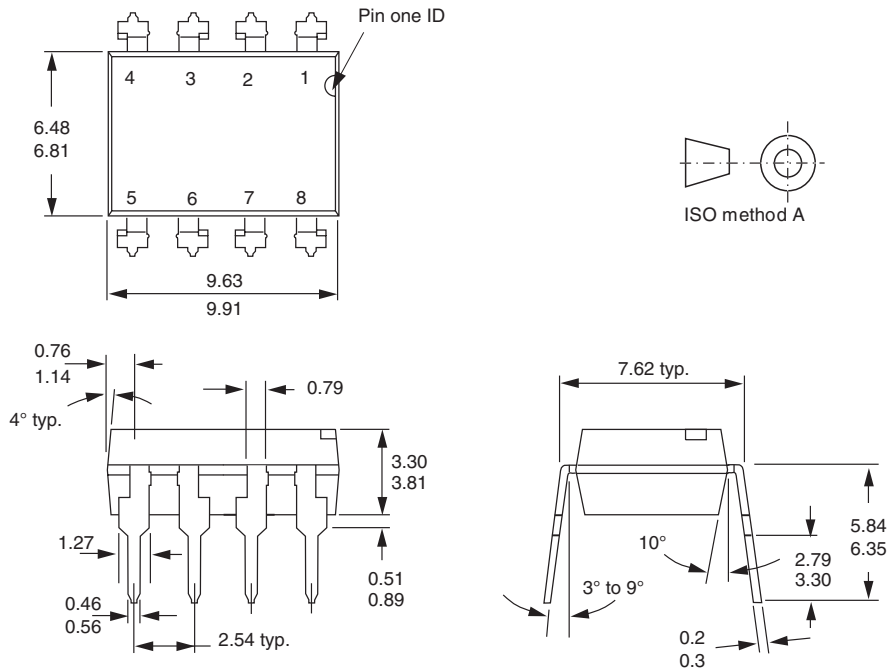
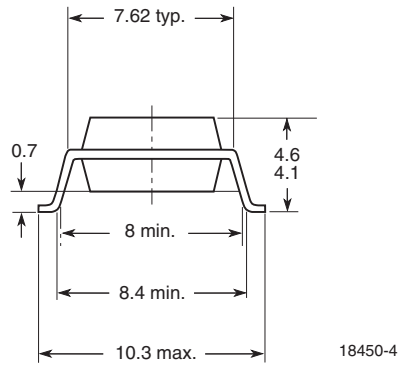
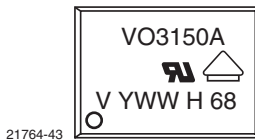


Fig. 21 - Propagation Delay vs. Forward LED Current

PACKAGE DIMENSIONS in millimeters


i178006

Option 7

PACKAGE MARKING

Note

- VDE logo is only marked on option 1 parts. Option information is not marked on the part.



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